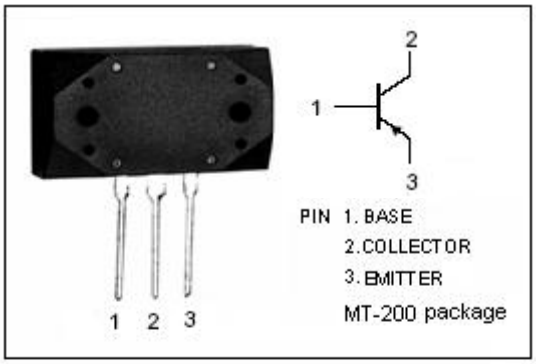
isc Silicon PNP Power Transistor — 2SA1169

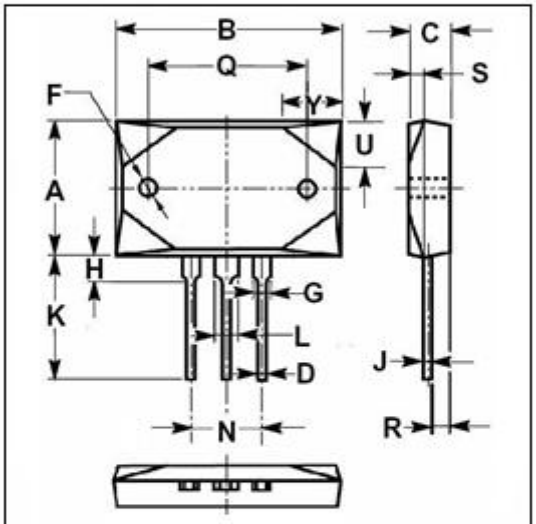


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  $V_{(BR)CEO}$= -200V(Min)
- High Power Dissipation
- Complement to Type 2SC2773
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for power amplifier and general purpose applications.



DIM	mm MIN	mm MAX
A	21.00	21.70
B	35.80	36.70
C	5.60	6.20
D	1.04	1.07
F	3.10	3.50
G	1.90	2.40
H	3.60	4.00
J	0.55	0.85
K	20.00	20.80
L	2.90	3.40
N	10.50	11.10
Q	24.00	24.50
R	2.90	3.30
S	2.00	2.20
U	6.90	7.10
Y	8.90	9.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-200	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-15	A
P_C	Collector Power Dissipation @ T_C=25℃	150	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -50mA; I_B= 0	-200			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E=-1mA; I_C=0	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -10A; I_B= -1A			-2.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -200V; I_E= 0			-100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -6V; I_C= 0			-100	μA
h_{FE}	DC Current Gain	I_C= -5A; V_{CE}= -4V	30		200	
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V; f_{test}= 1.0MHz		400		pF
f_T	Current-Gain—Bandwidth Product	I_E= 1A; V_{CE}= -12V		20		MHz